

# 74LVC2G14

## Dual inverting Schmitt trigger with 5 V tolerant input

Rev. 04 — 4 September 2007

Product data sheet

### 1. General description

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The 74LVC2G14 provides two inverting buffers with Schmitt-trigger action.

The inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of this device in a mixed 3.3 V and 5 V environment. Schmitt-trigger action at the inputs makes the circuit tolerant of slower input rise and fall time. This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

### 2. Features

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- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant inputs for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
  - ◆ JESD8-7 (1.65 V to 1.95 V)
  - ◆ JESD8-5 (2.3 V to 2.7 V)
  - ◆ JESD8B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - ◆ HBM JESD22-A114E exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
- $\pm 24$  mA output drive ( $V_{CC} = 3.0$  V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Unlimited rise and fall times
- Input accepts voltages up to 5 V
- Multiple package options
- Specified from  $-40$  °C to  $+85$  °C and  $-40$  °C to  $+125$  °C.

### 3. Applications

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- Wave and pulse shaper
- Astable multivibrator
- Monostable multivibrator

## 4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74LVC2G14GW	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74LVC2G14GV	-40 °C to +125 °C	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457
74LVC2G14GM	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74LVC2G14GF	-40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

## 5. Marking

Table 2. Marking

Type number	Marking code
74LVC2G14GW	VK
74LVC2G14GV	V14
74LVC2G14GM	VK
74LVC2G14GF	VK

## 6. Functional diagram

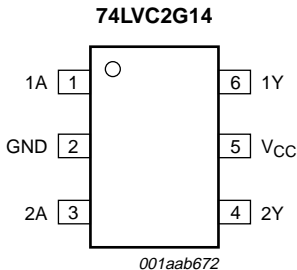
**Fig 1. Logic symbol**

**Fig 2. IEC logic symbol**

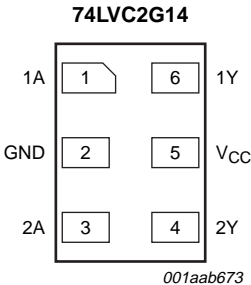
**Fig 3. Logic diagram**

## 7. Pinning information

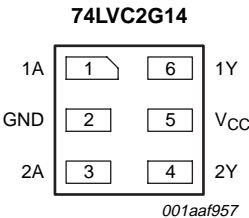
### 7.1 Pinning



**74LVC2G14**  
001aab672



**74LVC2G14**  
001aab673  
Transparent top view



**74LVC2G14**  
001aaf957  
Transparent top view

**Fig 4. Pin configuration SOT363 and SOT457**

**Fig 5. Pin configuration SOT886**

**Fig 6. Pin configuration SOT891**

### 7.2 Pin description

**Table 3. Pin description**

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V <sub>CC</sub>	5	supply voltage
1Y	6	data input

## 8. Functional description

**Table 4. Function table<sup>[1]</sup>**

Input	Output
nA	nY
L	H
H	L

[1] H = HIGH voltage level;  
L = LOW voltage level.

## 9. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+6.5	V
$I_{IK}$	input clamping current	$V_I < 0$ V	-50	-	mA
$V_I$	input voltage		[1] -0.5	+6.5	V
$I_{OK}$	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	$\pm 50$	mA
$V_O$	output voltage	Active mode	[1][2] -0.5	$V_{CC} + 0.5$	V
		Power-down mode	[1][2] -0.5	+6.5	V
$I_O$	output current	$V_O = 0$ V to $V_{CC}$	-	$\pm 50$	mA
$I_{CC}$	supply current		-	100	mA
$I_{GND}$	ground current		-100	-	mA
$P_{tot}$	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[3] -	250	mW
$T_{stg}$	storage temperature		-65	+150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When  $V_{CC} = 0$  V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For SC-88 and SC-74A packages: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.  
For XSON6 packages: above 45 °C the value of  $P_{tot}$  derates linearly with 2.4 mW/K.

## 10. Recommended operating conditions

**Table 6. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CC}$	supply voltage		1.65	-	5.5	V
$V_I$	input voltage		0	-	5.5	V
$V_O$	output voltage	Active mode	0	-	$V_{CC}$	V
		Power-down mode; $V_{CC} = 0$ V	0	-	5.5	V
$T_{amb}$	ambient temperature		-40	-	+125	°C

## 11. Static characteristics

**Table 7. Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -4 mA; V <sub>CC</sub> = 1.65 V	1.2	-	-	V
		I <sub>O</sub> = -8 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.7 V	2.2	-	-	V
		I <sub>O</sub> = -24 mA; V <sub>CC</sub> = 3.0 V	2.3	-	-	V
		I <sub>O</sub> = -32 mA; V <sub>CC</sub> = 4.5 V	3.8	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.45	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.3	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.4	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.55	V
		I <sub>O</sub> = 32 mA; V <sub>CC</sub> = 4.5 V	-	-	0.55	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	±0.1	±5	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>I</sub> or V <sub>O</sub> = 5.5 V; V <sub>CC</sub> = 0 V	-	±0.1	±10	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 1.65 V to 5.5 V; I <sub>O</sub> = 0 A	-	0.1	10	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 2.3 V to 5.5 V	-	5	500	μA
C <sub>I</sub>	input capacitance	V <sub>CC</sub> = 3.3 V; V <sub>I</sub> = GND to V <sub>CC</sub>	-	3.5	-	pF
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -4 mA; V <sub>CC</sub> = 1.65 V	0.95	-	-	V
		I <sub>O</sub> = -8 mA; V <sub>CC</sub> = 2.3 V	1.7	-	-	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.7 V	1.9	-	-	V
		I <sub>O</sub> = -24 mA; V <sub>CC</sub> = 3.0 V	2.0	-	-	V
		I <sub>O</sub> = -32 mA; V <sub>CC</sub> = 4.5 V	3.4	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.7	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.6	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.8	V
		I <sub>O</sub> = 32 mA; V <sub>CC</sub> = 4.5 V	-	-	0.8	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = 5.5 V or GND; V <sub>CC</sub> = 0 V to 5.5 V	-	-	±20	μA

**Table 7. Static characteristics ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ [1]	Max	Unit
$I_{OFF}$	power-off leakage current	$V_I$ or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	-	$\pm 20$	$\mu$ A
$I_{CC}$	supply current	$V_I = 5.5$ V or GND; $V_{CC} = 1.65$ V to 5.5 V; $I_O = 0$ A	-	-	40	$\mu$ A
$\Delta I_{CC}$	additional supply current	$V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 2.3$ V to 5.5 V	-	-	5000	$\mu$ A

[1] All typical values are measured at maximum  $V_{CC}$  and  $T_{amb} = 25$  °C.

**Table 8. Transfer characteristics**

Voltages are referenced to GND (ground = 0 V; for test circuit see [Figure 8](#))

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ [1]	Max	Min	Max	
$V_{T+}$	positive-going threshold voltage	see <a href="#">Figure 9</a> and <a href="#">Figure 10</a>						
		$V_{CC} = 1.8$ V	0.70	1.10	1.50	0.70	1.70	V
		$V_{CC} = 2.3$ V	1.00	1.40	1.80	1.00	2.00	V
		$V_{CC} = 3.0$ V	1.30	1.76	2.20	1.30	2.40	V
		$V_{CC} = 4.5$ V	1.90	2.47	3.10	1.90	3.30	V
$V_{T-}$	negative-going threshold voltage	see <a href="#">Figure 9</a> and <a href="#">Figure 10</a>						
		$V_{CC} = 1.8$ V	0.25	0.61	0.90	0.25	1.10	V
		$V_{CC} = 2.3$ V	0.40	0.80	1.15	0.40	1.35	V
		$V_{CC} = 3.0$ V	0.60	1.04	1.50	0.60	1.70	V
		$V_{CC} = 4.5$ V	1.00	1.55	2.00	1.00	2.20	V
$V_H$	hysteresis voltage	$(V_{T+} - V_{T-})$ ; see <a href="#">Figure 9</a> , <a href="#">Figure 10</a> and <a href="#">Figure 11</a>						
		$V_{CC} = 1.8$ V	0.15	0.49	1.00	0.15	1.20	V
		$V_{CC} = 2.3$ V	0.25	0.60	1.10	0.25	1.30	V
		$V_{CC} = 3.0$ V	0.40	0.73	1.20	0.40	1.40	V
		$V_{CC} = 4.5$ V	0.60	0.92	1.50	0.60	1.70	V
		$V_{CC} = 5.5$ V	0.70	1.02	1.70	0.70	1.90	V

[1] All typical values are measured at  $T_{amb} = 25$  °C

## 12. Dynamic characteristics

**Table 9. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
t <sub>pd</sub>	propagation delay	nA to nY; see <a href="#">Figure 7</a> <sup>[2]</sup>						
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.0	5.6	11.0	1.0	12.0	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.5	3.7	6.5	0.5	7.2	ns
		V <sub>CC</sub> = 2.7 V	0.5	4.1	7.0	0.5	7.7	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	0.5	3.9	6.0	0.5	6.7	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.5	2.7	4.3	0.5	4.7	ns
C <sub>PD</sub>	power dissipation capacitance	V <sub>I</sub> = GND to V <sub>CC</sub> ; V <sub>CC</sub> = 3.3 V <sup>[3]</sup>	-	18.1	-	-	-	pF

[1] Typical values are measured at T<sub>amb</sub> = 25 °C and V<sub>CC</sub> = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.

[2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.

[3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

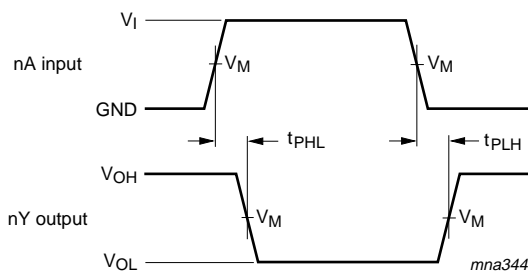
C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

∑(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of outputs.

## 13. Waveforms



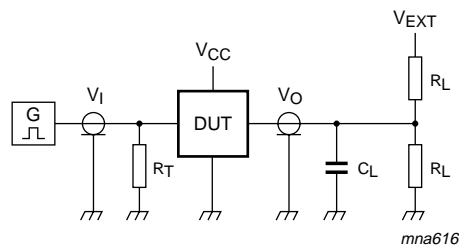
Measurement points are given in [Table 10](#).

V<sub>OL</sub> and V<sub>OH</sub> are typical output voltage levels that occur with the output load.

**Fig 7. The data input (nA) to output (nY) propagation delays**

Table 10. Measurement points

Supply voltage	Input	Output
$V_{CC}$	$V_M$	$V_M$
1.65 V to 1.95 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$



Test data is given in [Table 11](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance should be equal to the output impedance  $Z_o$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

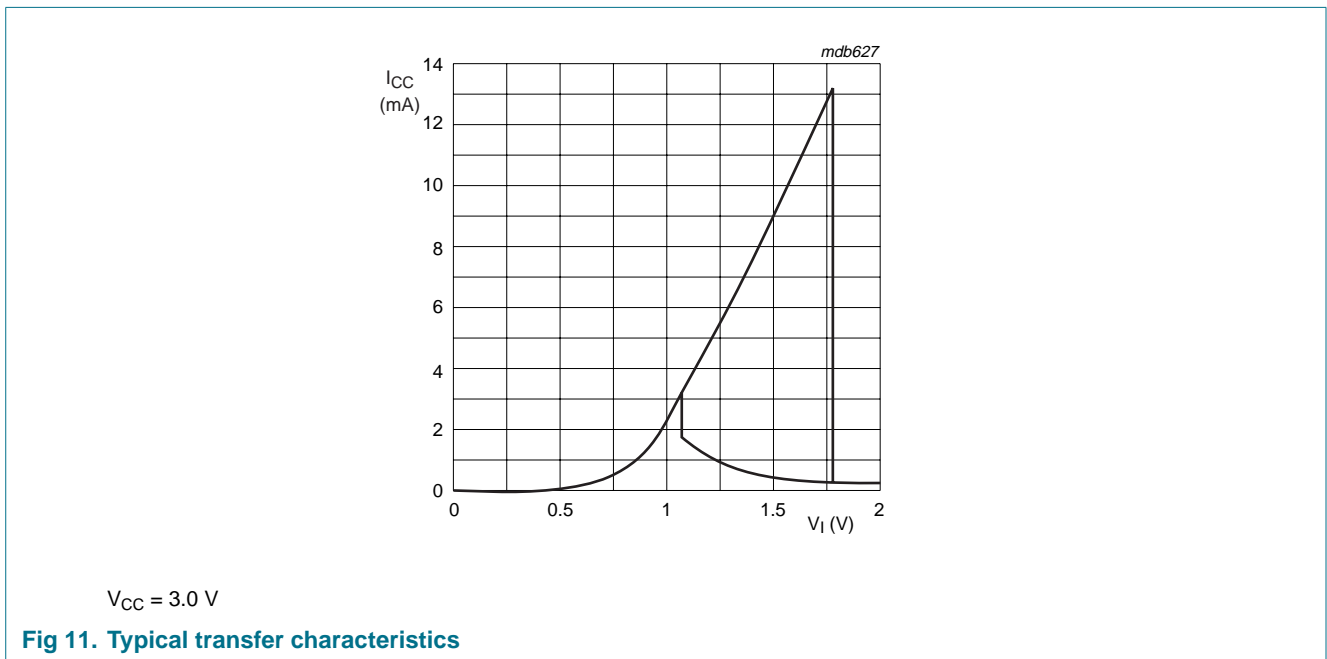
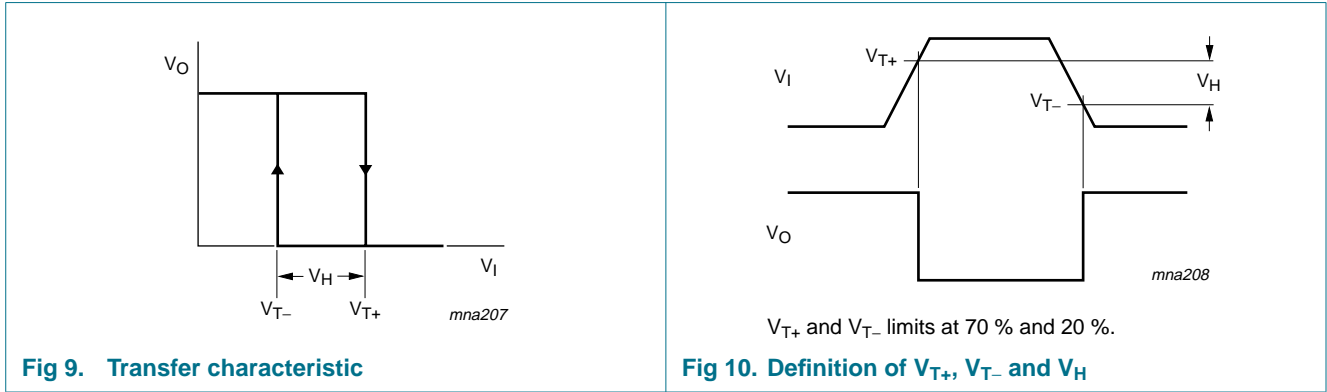
Fig 8. Load circuitry for switching times

Table 11. Test data

Supply voltage	Input	Load			$V_{EXT}$
$V_{CC}$	$V_I$	$t_r = t_f$	$C_L$	$R_L$	$t_{PLH}, t_{PHL}$
1.65 V to 1.95 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	1 k $\Omega$	open
2.3 V to 2.7 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	500 $\Omega$	open
2.7 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open
3.0 V to 3.6 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open
4.5 V to 5.5 V	$V_{CC}$	$\leq 2.5$ ns	50 pF	500 $\Omega$	open



14. Waveforms transfer characteristics



### 15. Application information

The slow input rise and fall times cause additional power dissipation, which can be calculated using the following formula:

$$P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC} \text{ where:}$$

$P_{add}$  = additional power dissipation ( $\mu W$ );

$f_i$  = input frequency (MHz);

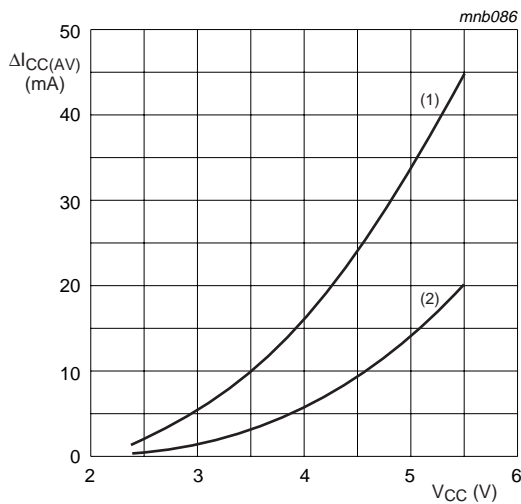
$t_r$  = input rise time (ns); 10 % to 90 %;

$t_f$  = input fall time (ns); 90 % to 10 %;

$\Delta I_{CC(AV)}$  = average additional supply current ( $\mu A$ ).

$\Delta I_{CC(AV)}$  differs with positive or negative input transitions, as shown in [Figure 12](#).

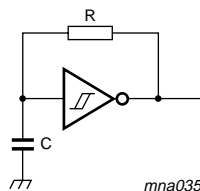
An example of a relaxation circuit using the 74LVC2G14 is shown in [Figure 13](#).



Linear change of  $V_I$  between 0.8 V to 2.0 V. All values given are typical unless otherwise specified.

- (1) Positive-going edge.
- (2) Negative-going edge.

**Fig 12. Average  $I_{CC}$  as a function of  $V_{CC}$**



$$f = \frac{1}{T} \approx \frac{1}{0.8 \times RC}$$

**Fig 13. Relaxation oscillator**

16. Package outline

Plastic surface-mounted package; 6 leads

SOT363

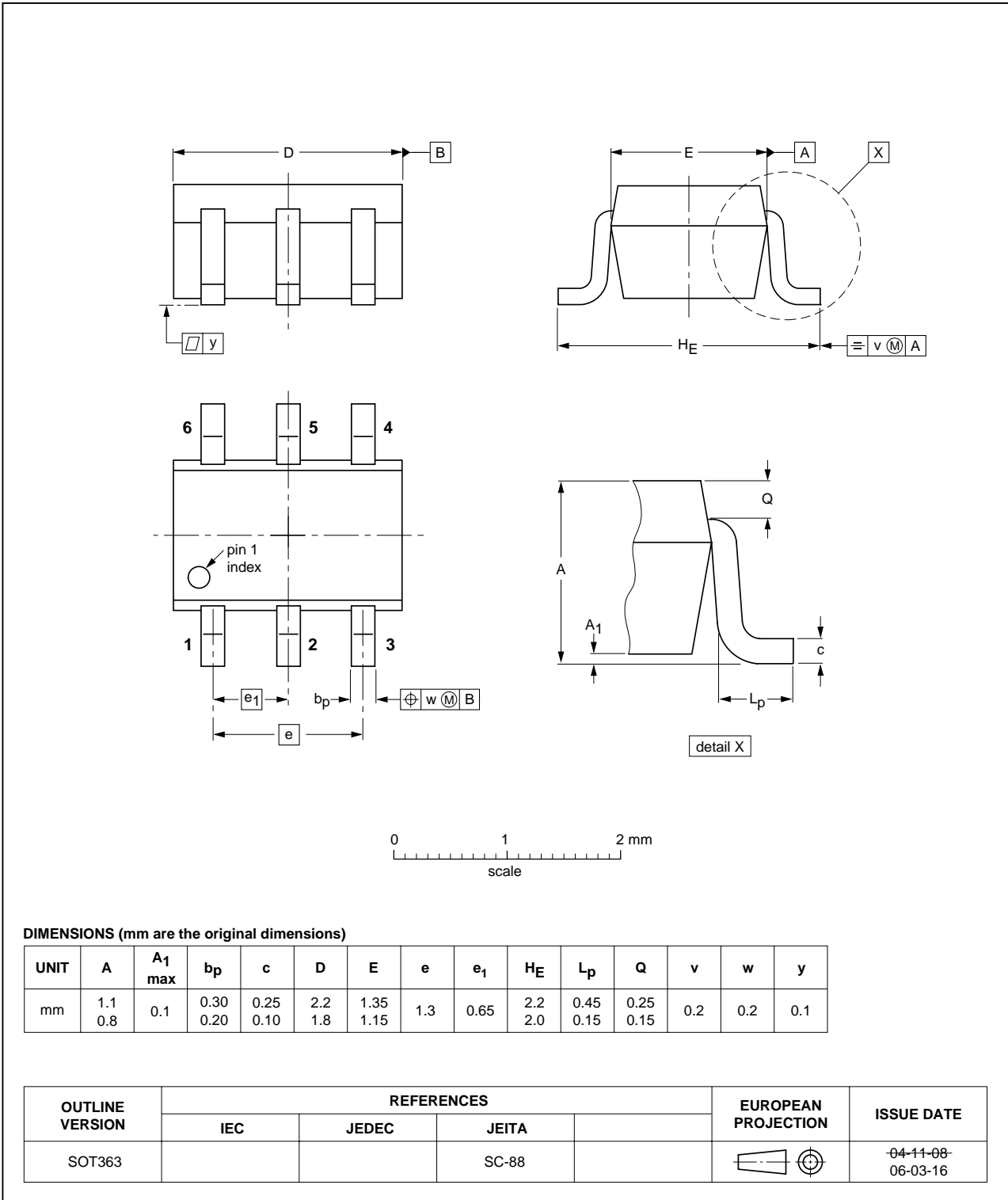


Fig 14. Package outline SOT363 (SC-88)

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

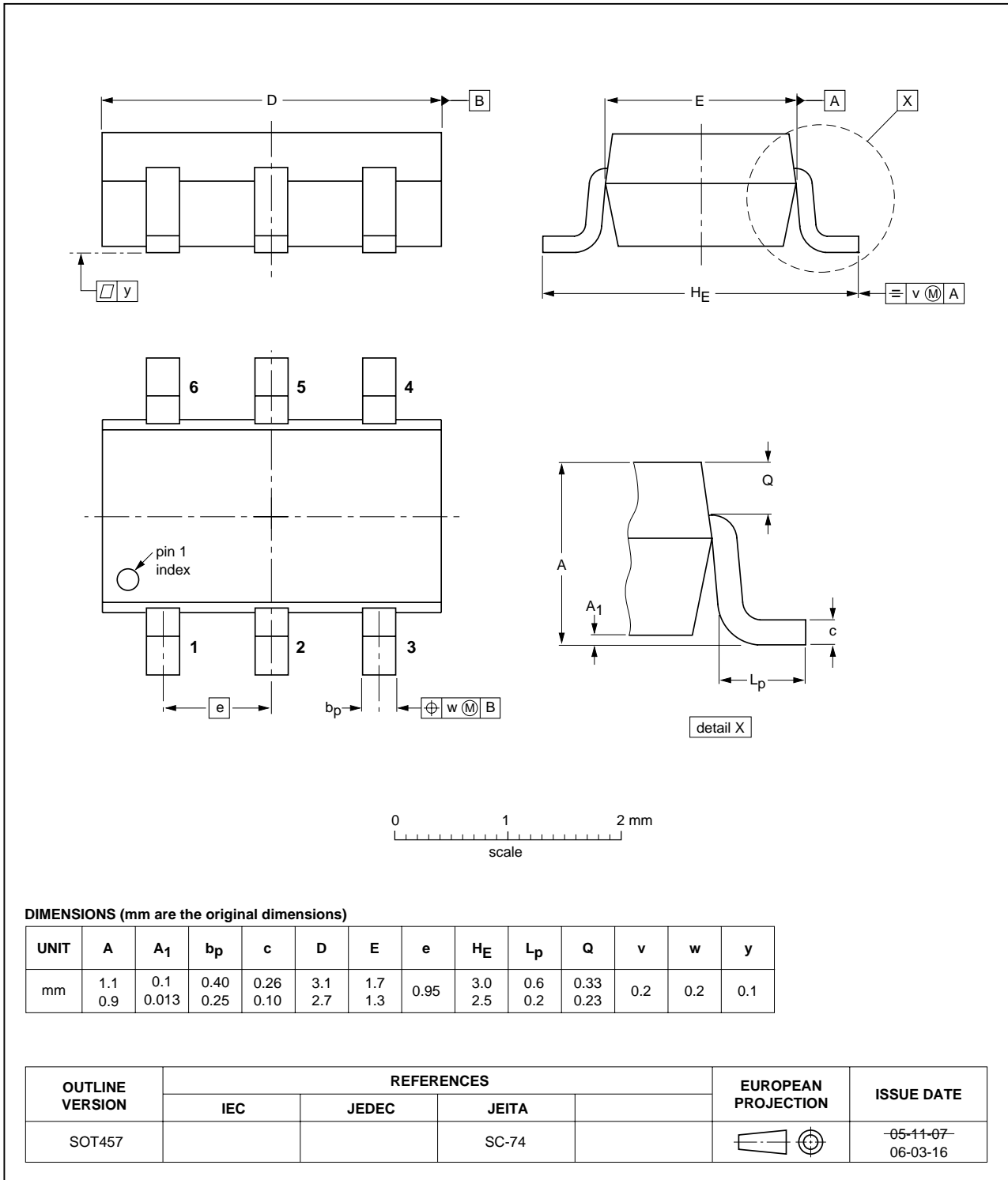


Fig 15. Package outline SOT457 (TSOP6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1.45 x 0.5 mm

SOT886



Fig 16. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891

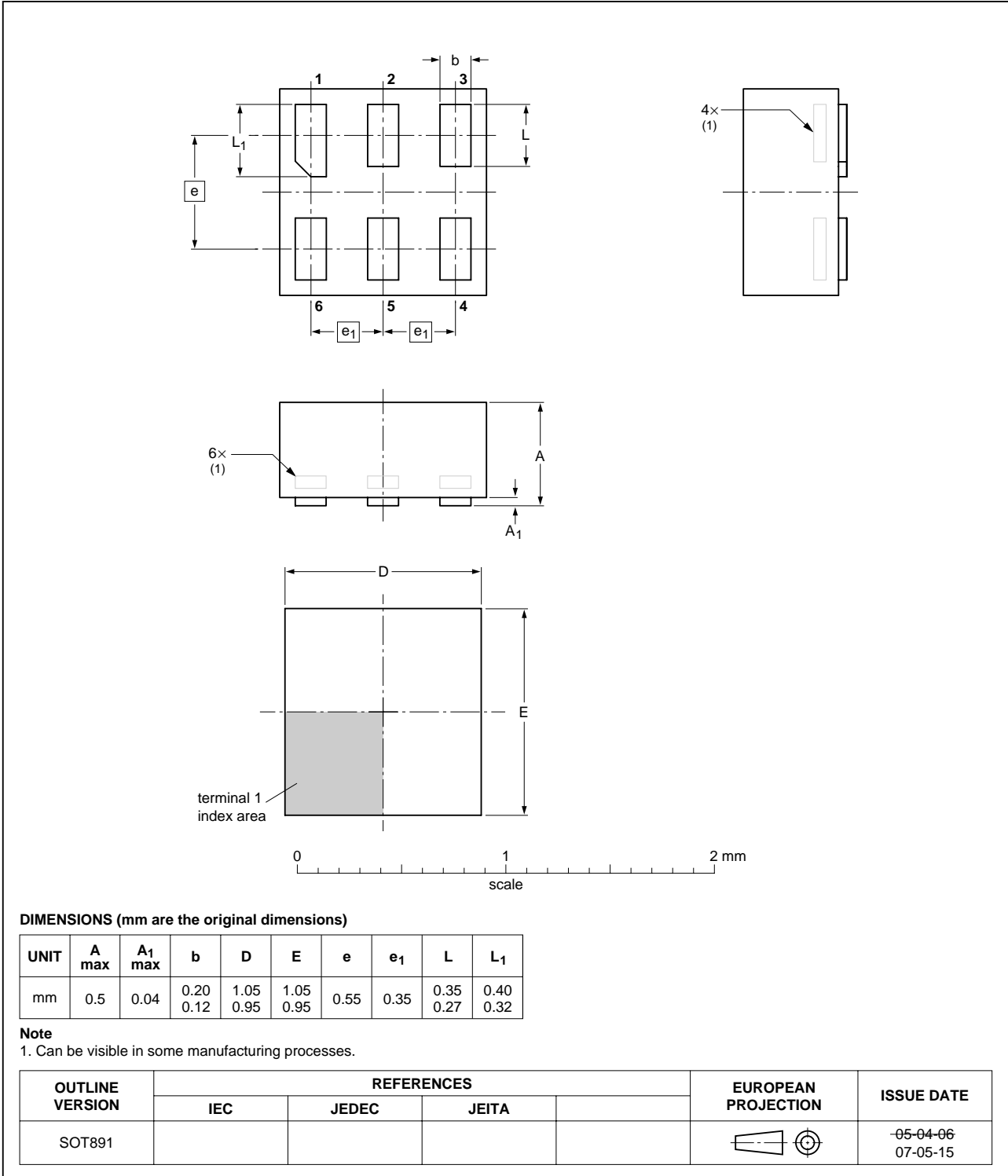


Fig 17. Package outline SOT891 (XSON6)

## 17. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test

## 18. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G14_4	20070904	Product data sheet		74LVC2G14_3
Modifications:		<ul style="list-style-type: none"> <li>In <a href="#">Section 11 “Static characteristics”</a>, changed conditions for input leakage and supply current.</li> <li><a href="#">Figure 17 “Package outline SOT891 (XSON6)”</a> updated.</li> </ul>		
74LVC2G14_3	20070220	Product data sheet		74LVC2G14_2
74LVC2G14_2	20040908	Product specification	-	74LVC2G14_1
74LVC2G14_1	20030731	Product specification		-

## 19. Legal information

### 19.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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